

● General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

● Features

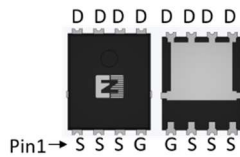
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low thermal resistance
- AEC-Q101 qualified

● Application

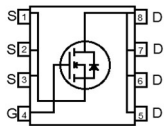
- BLDC motor driver
- DC-DC
- Load switch



● Product Summary



DFN5*6



$V_{DS}=40V$

$R_{DS(ON)}=1.2m\Omega$

$I_D=305A$



● Ordering Information

Part NO.	ZMSA010N04HNCW
Marking	ZMS010N04H
Packing information	REEL TAPE
Basic ordering unit (pcs)	3000

● Absolute Maximum Ratings ($T_A=25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Max.	Unit
Drain-source voltage	V_{DS}	$25^\circ\text{C} \leq T_J \leq 175^\circ\text{C}$	-	40	V
Gate-source voltage ^①	V_{GS}	DC; $-55^\circ\text{C} \leq T_J \leq 175^\circ\text{C}$	-20	20	V
Continuous drain current	I_D	$V_{GS}=10V, T_C=25^\circ\text{C}$	-	305	A
	I_D	$V_{GS}=10V, T_C=75^\circ\text{C}$	-	249	A
	I_D	$V_{GS}=10V, T_C=100^\circ\text{C}$	-	215	A
Pulsed drain current	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}; T_C = 25^\circ\text{C}$	-	1220	A
Diode continuous current	I_S	$V_{GS}=0V, T_C=25^\circ\text{C}$	-	189	A
Diode pulse current	$I_{S,pulse}$	$V_{GS}=0V$, Pulsed, $t_p \leq 10 \mu\text{s}, T_C = 25^\circ\text{C}$	-	756	A
Total power dissipation	P_D	$V_{GS} > 6V, T_C=25^\circ\text{C}$	-	246	W
Total power dissipation	P_D	$V_{GS} > 6V, T_A=25^\circ\text{C}$	-	3.3	W
Operating junction temperature	T_J		-55	175	$^\circ\text{C}$
Storage temperature	T_{STG}		-55	175	$^\circ\text{C}$
Single pulse avalanche energy	E_{AS}	$L=0.1mH, V_{GS}=10V, R_g=25\Omega, V_{DD}=25V, I_{AS}=74A$	-	274	mJ

Single pulse avalanche energy	E_{AS}	$L=0.5mH, V_{GS}=10V, R_g=25\Omega, V_{DD}=25V,$ $I_{AS}=44.4A$	-	493	mJ
ESD level (HBM)	CLASS 2				

● Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	0.61	°C/W
Thermal resistance, junction - ambient	$R_{thJA}^{②}$	-	-	45	°C/W
Soldering temperature	T_{sold}	-	-	260	°C

● Electronic Characteristics ($T_j=25^\circ C$, unless otherwise specified)

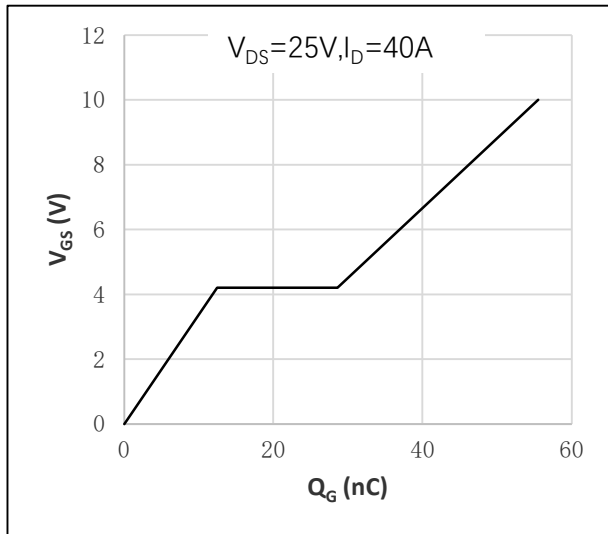
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A, T_j=25^\circ C$	40	-	-	V
		$V_{GS}=0V, I_D=1mA, T_j=-55^\circ C$	38.5	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2	2.6	4	V
		$V_{GS}=V_{DS}, I_D=1mA, T_j=175^\circ C$	1.2	-	-	V
		$V_{GS}=V_{DS}, I_D=1mA, T_j=-55^\circ C$	-	-	4.7	V
Drain-source leakage current	I_{DSS}	$V_{GS}=0V, V_{DS}=40V, T_j=25^\circ C$	-	-	1	μA
		$V_{GS}=0V, V_{DS}=40V, T_j=175^\circ C$	-	-	500	μA
Gate- source leakage current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	100	nA
Static drain-source on resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=40A, T_j=25^\circ C$	-	1.2	1.5	m Ω
		$V_{GS}=10V, I_D=40A, T_j=175^\circ C$	-	2.1	-	m Ω
Forward transconductance	g_{FS}	$V_{DS}=5V, I_D=10A$	-	21	-	S
Diode forward voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=40A$	-	0.8	1.3	V

● Dynamic characteristics ($T_j=25^\circ C$, unless otherwise specified)

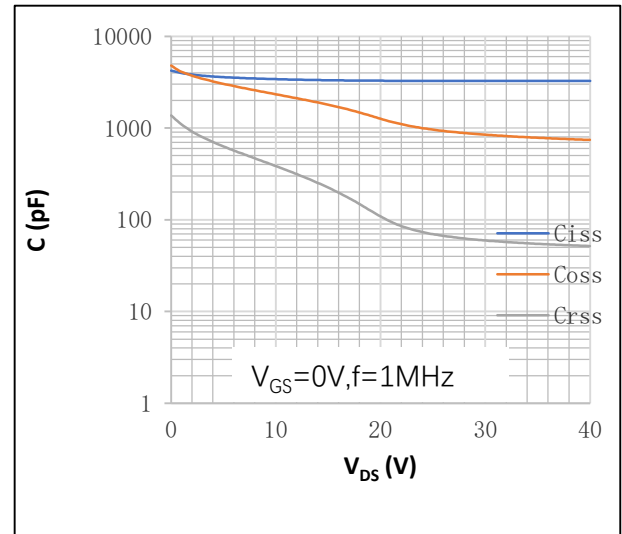
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V,$ $V_{GS}=0V$	-	3276	-	pF
Output capacitance	C_{oss}		-	964	-	pF
Reverse transfer capacitance	C_{rss}		-	70	-	pF
Gate resistance	R_g	$f=1MHz$	-	4.2	-	Ω
Total gate charge	Q_g	$V_{DD}=25V, I_D=40A,$ $V_{GS}=10V$	-	55.5	-	nC
Gate-source charge	Q_{gs}		-	12.5	-	nC
Gate-drain charge	Q_{gd}		-	16.1	-	nC

Turn-on delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=25V,$ $R_G=3.3\Omega, I_D=40A$	-	12	-	ns
Turn-on rise time	t_r		-	12	-	ns
Turn-off delay time	$t_{D(off)}$		-	35	-	ns
Turn-off fall time	t_f		-	23	-	ns
Reverse recovery time	t_{rr}	$V_{DD}=25V, di_s/dt = 100A/us,$ $I_S=40A$	-	43	-	ns
Reverse recovery charge	Q_{rr}		-	41	-	nC

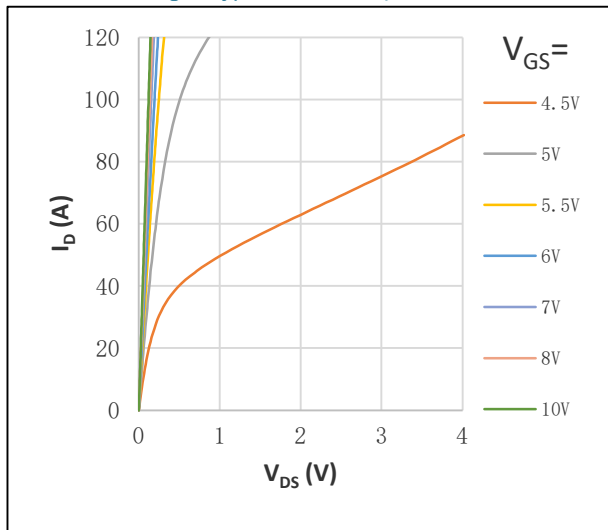
● Fig.1 Gate-source voltage as a function of gate charge; Typical values; $T_j=25^\circ\text{C}$



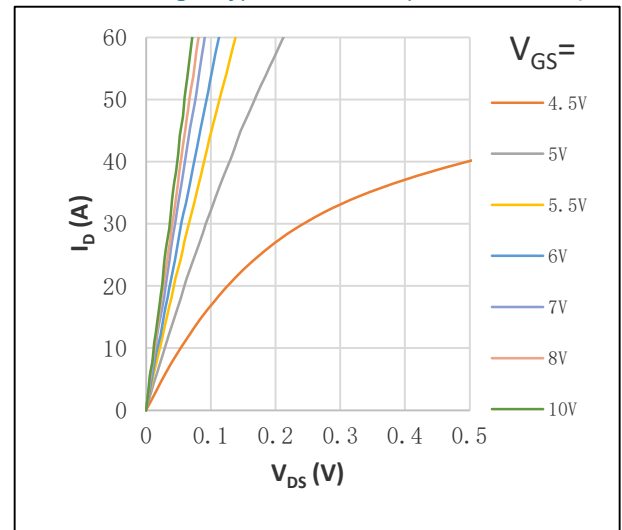
● Fig.2 Input, output and reverse transfer capacitances as a function of drain-source voltage; Typical values; $T_j=25^\circ\text{C}$



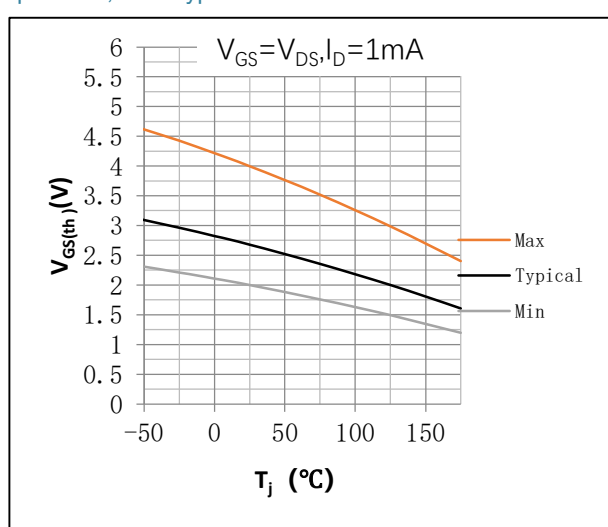
● Fig.3 Output characteristics: drain current as a function of drain-source voltage; Typical values; $T_j=25^\circ\text{C}$



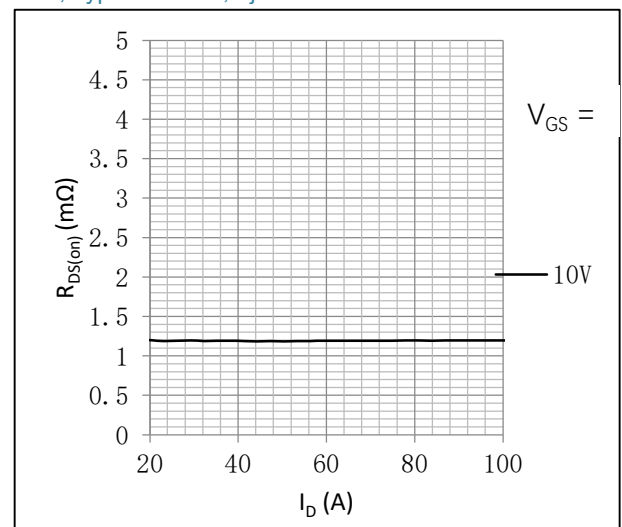
● Fig.4 Output characteristics: drain current as a function of drain-source voltage; Typical values: Expanded curve; $T_j=25^\circ\text{C}$



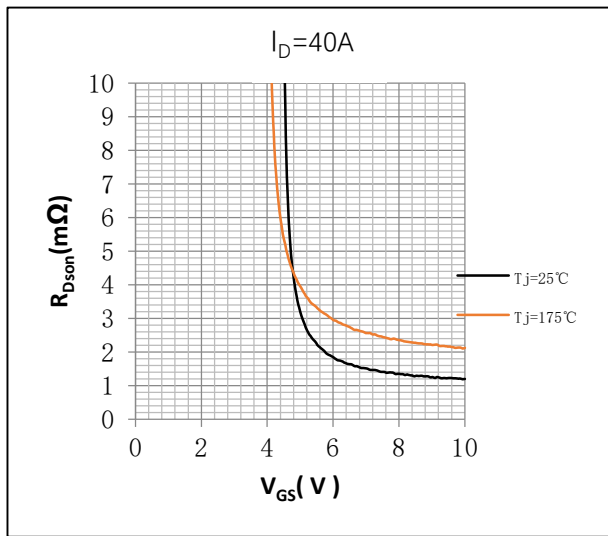
● Fig.5 Gate-source threshold voltage as a function of junction temperature; Max/Typical/Min values



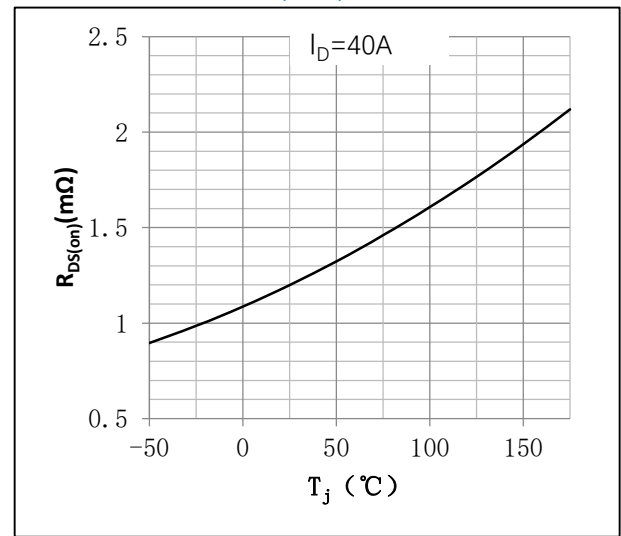
● Fig.6 Drain-source on-state resistance as a function of drain current; Typical values; $T_j=25^\circ\text{C}$



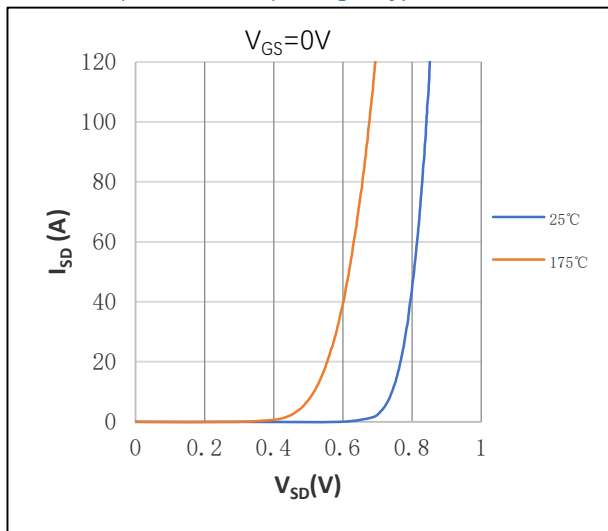
● Fig.7 Drain-source on-state resistance as a function of gate-source voltage; Typical values



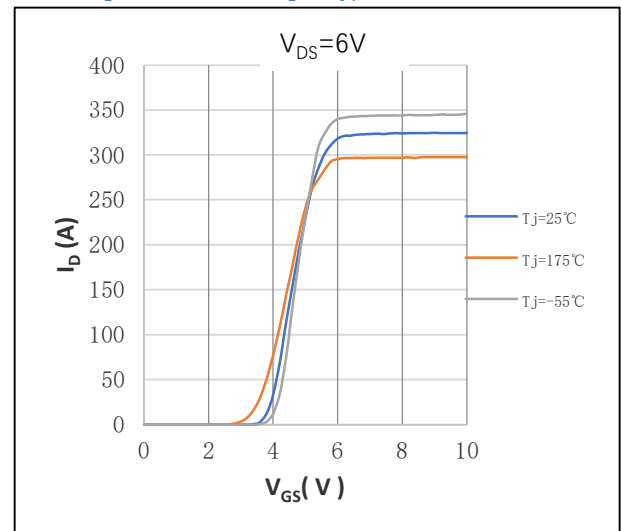
● Fig.8 Normalized drain-source on-state resistance factor as a function of junction temperature; Typical values Normalized On-Resistance = $R_{DS(on)}/R_{DS(on)}(25^{\circ}\text{C})$



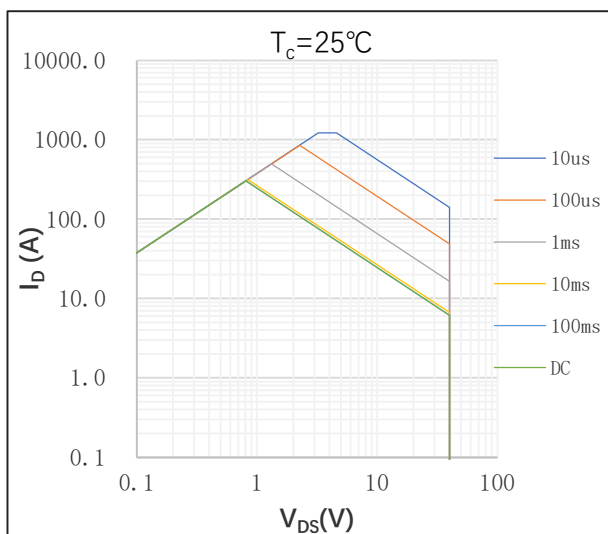
● Figure 9. Source (diode forward) current as a function of source-drain (diode forward) voltage; Typical values



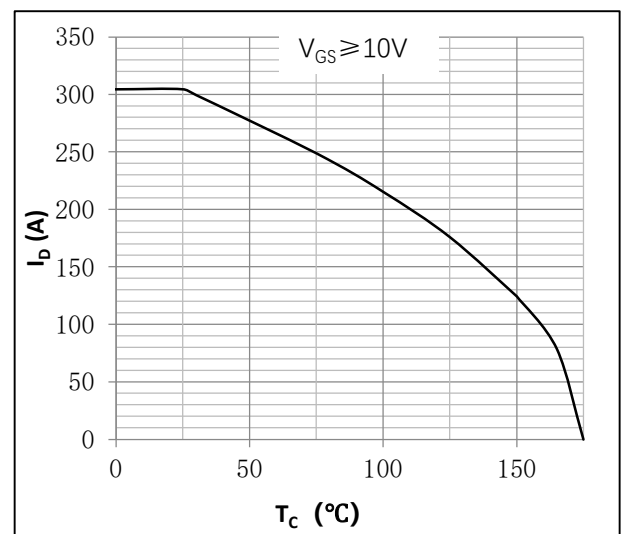
● Figure 10. Transfer characteristics: drain current as a function of gate-source voltage; Typical values



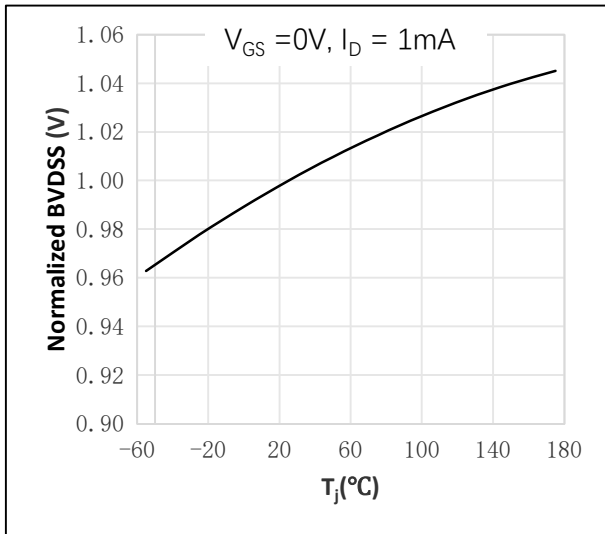
● Fig.11 Safe operating area: continuous and peak drain currents as a function of drain-source voltage; Calculative values



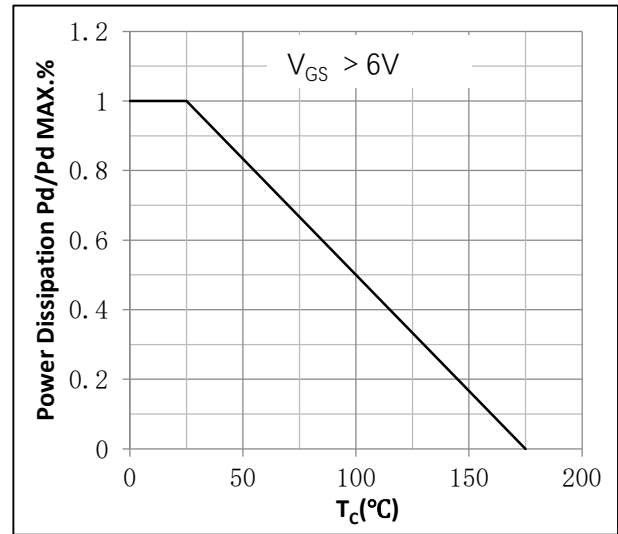
● Fig.12 Continuous drain current as a function of case temperature³; Calculative values



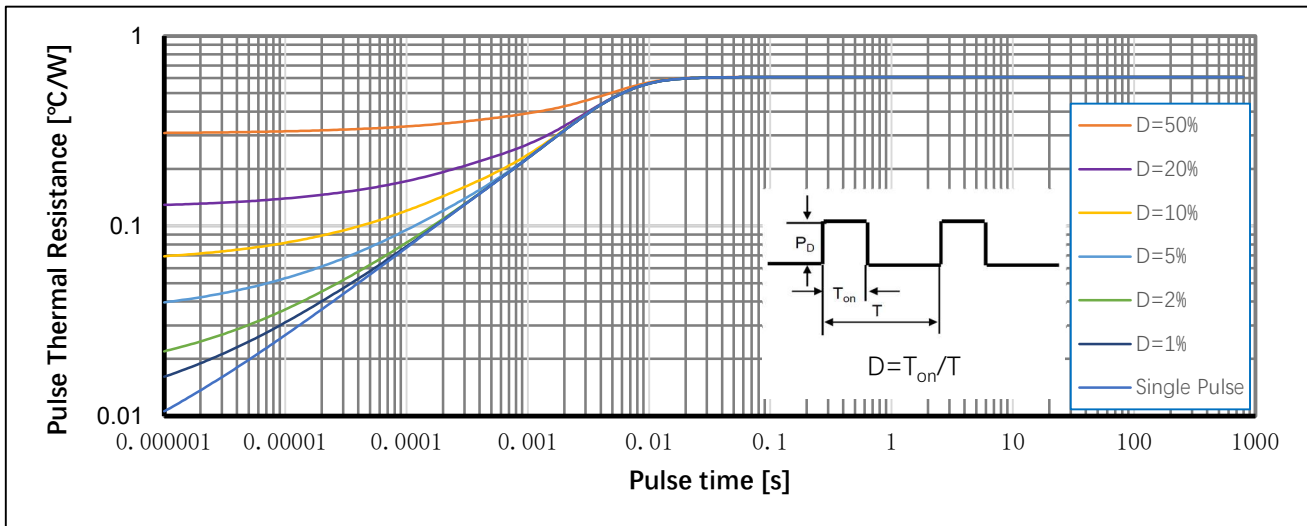
● Fig.13 Drain-source breakdown voltage as a function of junction temperature; Typical values Normalized $BV_{DSS} = BV_{DSS}/BV_{DSS}(25^{\circ}\text{C})$



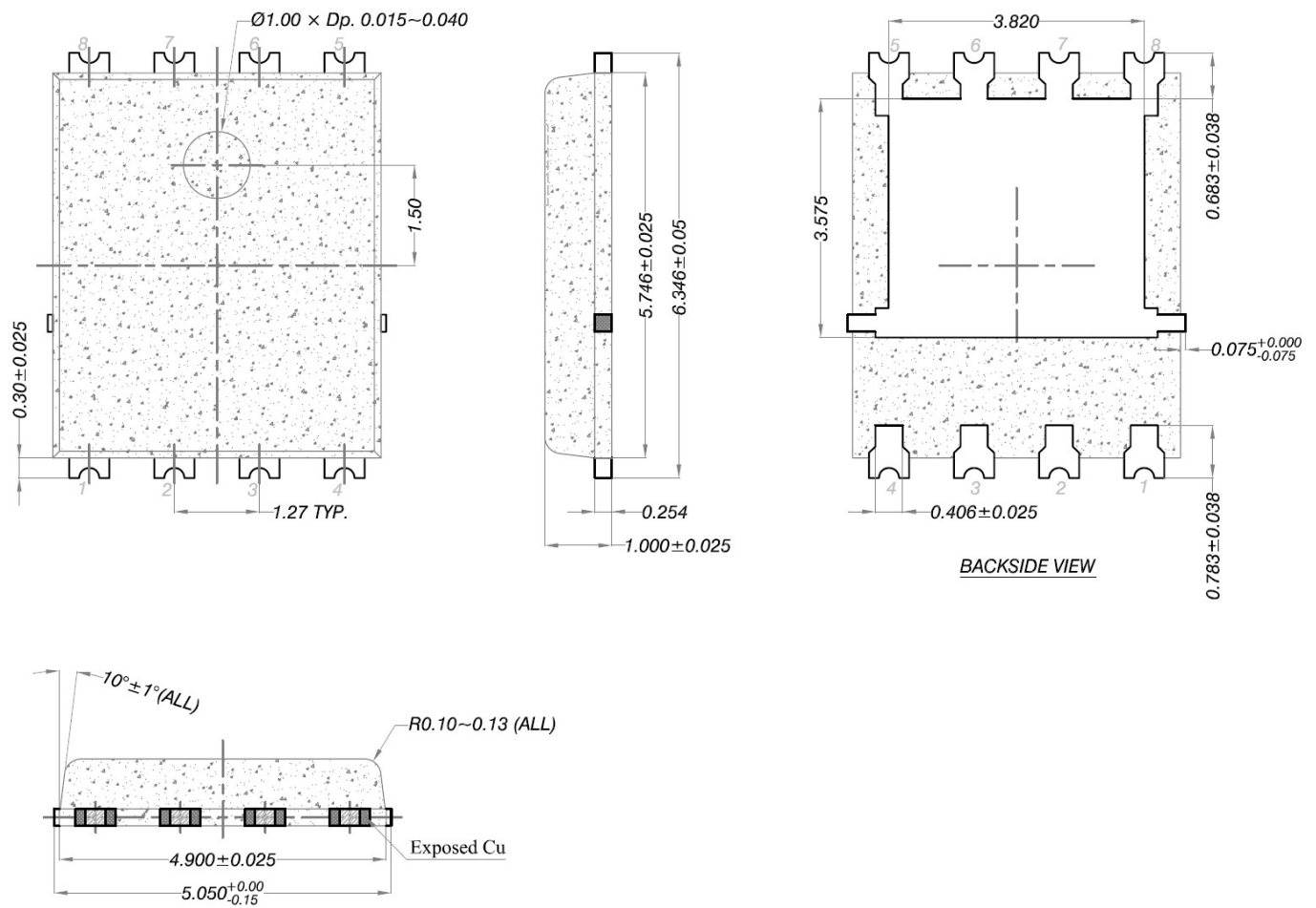
● Fig.14 Normalized total power dissipation as a function of case temperature; Calculative values Normalized Power Dissipation $= P_d/P_d(25^{\circ}\text{C})$



● Fig.15 Transient thermal impedance from junction to case as a function of pulse duration; max values



● Package Outline



● Note

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}C$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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● Revision History

Version	Date	Change
A	2026/5/20	New